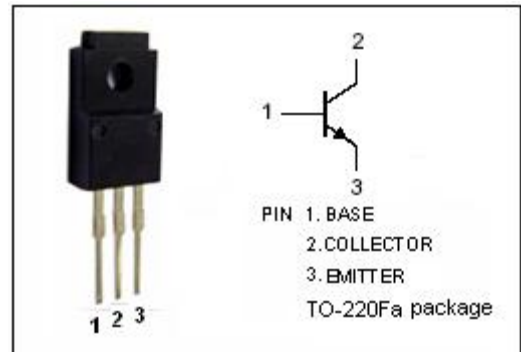


**isc Silicon NPN Power Transistor**
**2SC3475**
**DESCRIPTION**

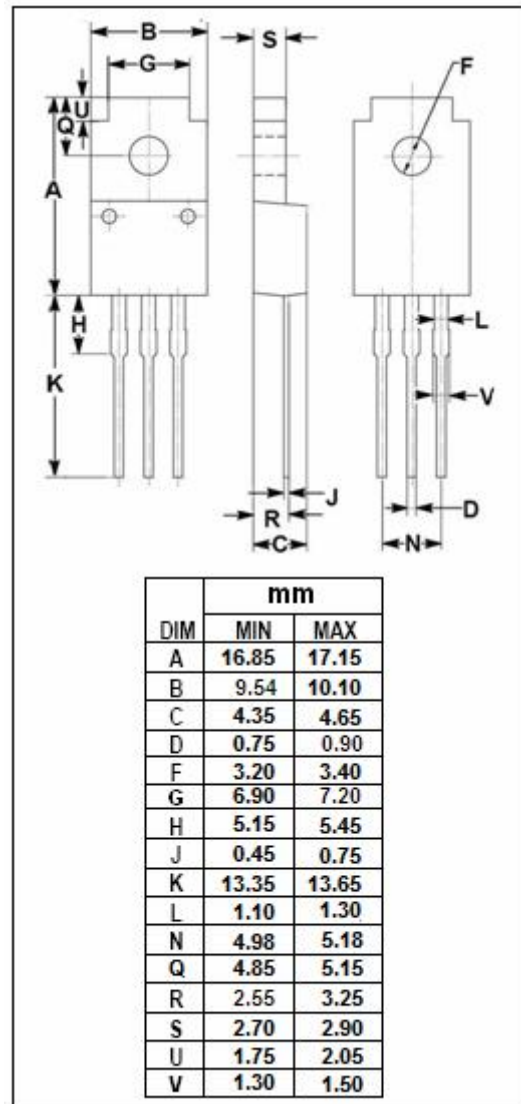
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = 0.6V(\text{Max}) @ I_C = 2A$
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- High speed switching applications.
- High speed DC-DC converter applications.


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	4	A
$I_{CM}$	Collector Current-Peak	8	A
$I_B$	Base Current-Continuous	1	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	20	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistor**
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**ELECTRICAL CHARACTERISTICS**
**T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			0.6	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	60		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 4V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 4V		20		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		70		pF

**Switching times**

t <sub>on</sub>	Turn-on Time	I <sub>B1</sub> = -I <sub>B2</sub> = 0.2A; R <sub>L</sub> = 15 Ω; V <sub>CC</sub> = 30V			0.5	μ s
t <sub>stg</sub>	Storage Time				2.5	μ s
t <sub>f</sub>	Fall Time				0.5	μ s

**◆ h<sub>FE-1</sub> classifications**

O	Y
60-120	100-200

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